

Title (en)
COMPENSATION FOR STRESS INDUCED RESISTANCE VARIATIONS

Title (de)
KOMPENSATION VON SPANNUNGSINDUZIERTEN WIDERSTANDSVERÄNDERUNGEN

Title (fr)
COMPENSATION DE VARIATION DE RÉSISTANCE INDUITES PAR UNE CONTRAINTE

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Application
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Abstract (en)
[origin: WO2012013977A1] According to the invention there is provided a method of compensating for stress induced variations in the resistance of a semiconductor resistor element, the method including the steps of: providing a semiconductor device which includes the semiconductor resistor element and a reference arrangement, in which the reference arrangement includes a metallic reference resistor (30) and a semiconductor reference resistor (32); generating a compensation parameter by measuring stress induced changes in the resistances of the metallic reference resistor and the semiconductor reference resistor, or at least one quantity functionally related thereto; and using the compensation parameter to compensate for stress induced variations in the resistance of the semiconductor resistor element.

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